4K x 4 Static RAM

Features

- **CMOS for optimum speed/power**
- **High speed**
  - **— t_{AA} = 15 ns**
  - **— t_{ACS} = 10 ns**
- **Low active power**
  - **— 495 mW (commercial)**
  - **— 660 mW (military)**
- **TTL-compatible inputs and outputs**
- **Capable of withstanding greater than 2001V electrostatic discharge**
- **Output enable**
- **V_{IH} of 2.2V**

Functional Description

The CY7C170A is a high-performance CMOS static RAM organized as 4096 words by 4 bits. Easy memory expansion is provided by an active LOW chip select ($\overline{CS}$), an active LOW output enable ($\overline{OE}$) and three-state drivers.

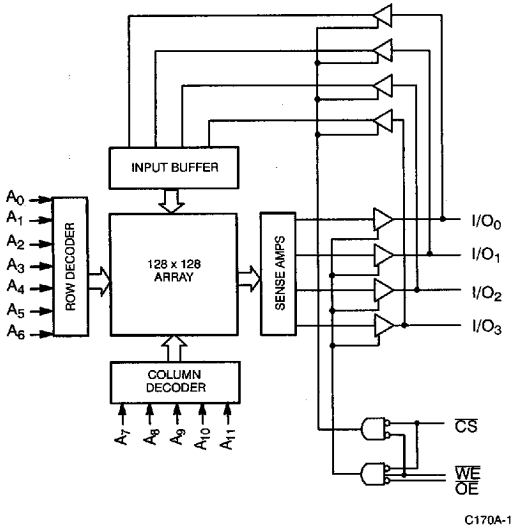
Writing to the device is accomplished when the chip select ($\overline{CS}$) and write enable ($\overline{WE}$) inputs are both LOW. Data on the four input/output pins (I/O_0 through I/O_3) is written into the memory location specified on the address pins (A_0 through A_{11}).

Reading the device is accomplished by taking chip select ($\overline{CS}$) and output enable ($\overline{OE}$) LOW, while write enable ($\overline{WE}$) remains HIGH. Under these conditions, the contents of the memory location specified on the address pins will appear on the four data I/O pins.

The I/O pins stay in high-impedance state when chip select ($\overline{CS}$) or output enable ($\overline{OE}$) is HIGH, or write enable ($\overline{WE}$) is LOW.

A die coat is used to ensure alpha immunity.

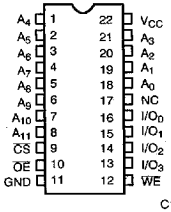
Logic Block Diagram



C170A-1

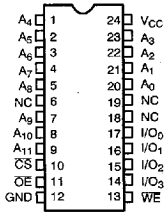
Pin Configurations

DIP
Top View



C170A-2

SOJ
Top View



C170A-3

Selection Guide

		7C170A–15	7C170A–20	7C170A–25	7C170A–35
Maximum Access Time (ns)		15	20	25	35
Maximum Operating Current (mA)	Commercial	115	90	90	90
	Military			120	

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature ..... −65°C to +150°C

Ambient Temperature with Power Applied ..... −55°C to +125°C

Supply Voltage to Ground Potential (Pin 22 to Pin 21) ..... −0.5V to +7.0V

DC Voltage Applied to Outputs in High Z State ..... −0.5V to +7.0V

DC Input Voltage ..... −3.0V to +7.0V

Output Current into Outputs (LOW) ..... 20 mA

Static Discharge Voltage ..... >2001V (per MIL-STD-883, Method 3015)

Latch-up Current ..... >200 mA

Operating Range

Range	Ambient Temperature	V_{CC}
Commercial	0°C to +70°C	5V ± 10%
Military[1]	−55°C to +125°C	5V ± 10%

Electrical Characteristics Over the Operating Range[2]

Parameter	Description	Test Conditions		7C170A−15 Min.	7C170A−15 Max.	7C170A−20, 25, 35, 45 Min.	7C170A−20, 25, 35, 45 Max.	Unit
V_{OH}	Output HIGH Voltage	V_{CC} = Min., I_{OH} = −4.0 mA		2.4		2.4		V
V_{OL}	Output LOW Voltage	V_{CC} = Min., I_{OL} = 8.0 mA			0.4		0.4	V
V_{IH}	Input HIGH Voltage			2.2	V_{CC}	2.2	V_{CC}	V
V_{IL}	Input LOW Voltage			−3.0	0.8	−3.0	0.8	V
I_{IX}	Input Load Current	GND ≤ V_I ≤ V_{CC}		−10	+10	−10	+10	μA
I_{OZ}	Output Leakage Current	GND ≤ V_O ≤ V_{CC}, Output Disabled		−10	+10	−10	+10	μA
I_{OS}	Output Short Circuit Current[3]	V_{CC} = Max., V_{OUT} = GND			−350		−350	mA
I_{CC}	V_{CC} Operating Supply Current	V_{CC} = Max. I_{OUT} = 0 mA	Com'l		115		90	mA
			Mil				120	mA

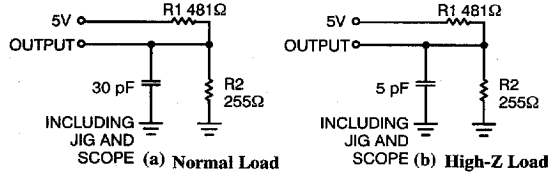
Capacitance[4]

Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = 5.0V	10	pF
C_{OUT}	Output Capacitance		10	pF

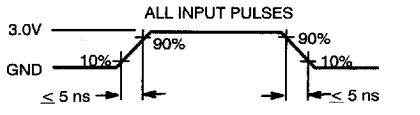
Notes:

1. T_A is the "instant on" case temperature.
2. See the last page of this specification for Group A subgroup testing information.
3. Not more than 1 output should be shorted at one time. Duration of the short circuit should not exceed 30 seconds.
4. Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms

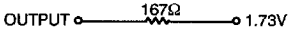


C170A-4



C170A-5

Equivalent to: THÉVENIN EQUIVALENT



Switching Characteristics Over the Operating Range[2, 5]

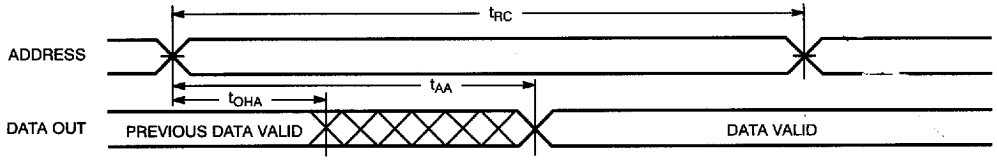
Parameter	Description	7C170A–15		7C170A–20		7C170A–25		7C170A–35		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
READ CYCLE										
t_{RC}	Read Cycle Time	15		20		25		35		ns
t_{AA}	Address to Data Valid		15		20		25		35	ns
t_{OHA}	Data Hold from Address Change	5		5		5		5		ns
t_{ACS}	$\overline{CS}$ LOW to Data Valid		10		15		15		25	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		10		10		12		15	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z	3		3		3		3		ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z[6]		8		8		10		12	ns
t_{LZCS}	$\overline{CS}$ LOW to Low Z[7]	5		5		5		5		ns
t_{HZCS}	$\overline{CS}$ HIGH to High Z[6, 7]		8		8		10		15	ns
WRITE CYCLE[8]										
t_{WC}	Write Cycle Time	15		20		20		25		ns
t_{SCS}	$\overline{CS}$ LOW to Write End	12		15		20		25		ns
t_{AW}	Address Set-Up to Write End	12		15		20		25		ns
t_{HA}	Address Hold from Write End	0		0		0		0		ns
t_{SA}	Address Set-Up to Write Start	0		0		0		0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	12		15		15		20		ns
t_{SD}	Data Set-Up to Write End	10		10		10		15		ns
t_{HD}	Data Hold from Write End	0		0		0		0		ns
t_{HZWE}	$\overline{WE}$ HIGH to High Z		7		7		7		10	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low Z	5		5		5		5		ns

Notes:

5. Test conditions assume signal transition times of 5 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V and output loading of the specified I_{OL}/I_{OH}, and 30-pF load capacitance.
6. t_{HZCE} and t_{HZWE} are tested with C_L = 5pF as in part (b) of AC Test Loads. Transition is measured ±500 mV from steady state voltage.
7. At any given temperature and voltage condition, t_{HZCS} is less than t_{LZCS} for any given device. These parameters are sampled and not 100% tested.
8. The internal write time of the memory is defined by the overlap of $\overline{CS}$ LOW and $\overline{WE}$ LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.
9. $\overline{WE}$ is HIGH for read cycle.
10. Device is continuously selected, $\overline{CS}$ = V_{IL} and $\overline{OE}$ = V_{IL}.

Switching Waveforms

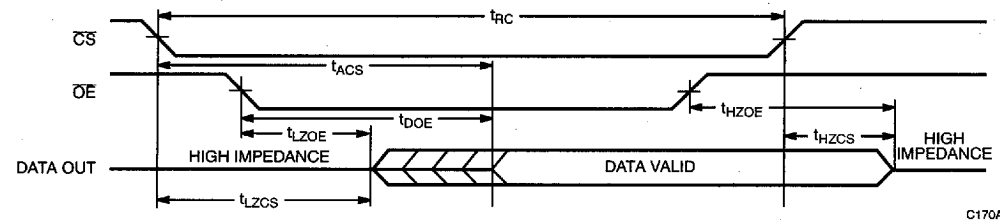
Read Cycle No. 1[9, 10]



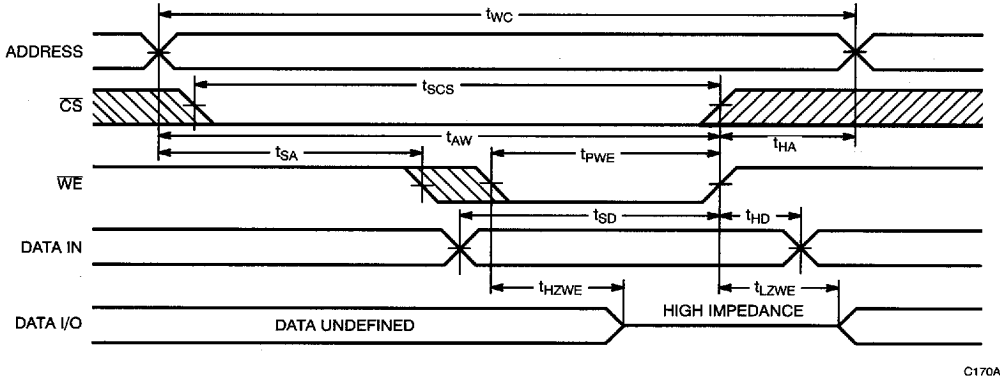
C170A-6

Switching Waveforms (continued)

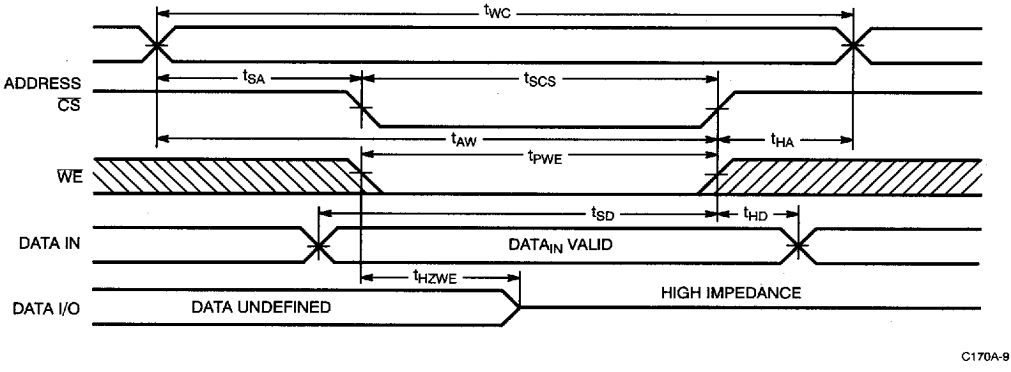
Read Cycle No. 2[9, 11]



Write Cycle No. 1[8, 12]



Write Cycle No. 2[8, 12, 13]



Notes:
11. Data I/O will be high-impedance if $\overline{OE} = V_{IH}$.
12. Address valid prior to or coincident with $\overline{CS}$ transition LOW.
13. If $\overline{CS}$ goes HIGH simultaneously with $\overline{WE}$ HIGH, the output remains in a high-impedance state.

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
15	CY7C170A–15PC	P9	22-Lead (300-Mil) Molded DIP	Commercial
	CY7C170A–15VC	V13	24-Lead Molded SOJ	
20	CY7C170A–20PC	P9	22-Lead (300-Mil) Molded DIP	Commercial
	CY7C170A–20VC	V13	24-Lead Molded SOJ	
25	CY7C170A–25PC	P9	22-Lead (300-Mil) Molded DIP	Commercial
	CY7C170A–25VC	V13	24-Lead Molded SOJ	
	CY7C170A–25DMB	D10	22-Lead (300-Mil) CerDIP	Military
35	CY7C170A–35PC	P9	22-Lead (300-Mil) Molded DIP	Commercial
	CY7C170A–35VC	V13	24-Lead Molded SOJ	

MILITARY SPECIFICATIONS

Group A Subgroup Testing

DC Characteristics

Parameter	Subgroups
V_{OH}	1, 2, 3
V_{OL}	1, 2, 3
V_{IH}	1, 2, 3
V_{IL} Max.	1, 2, 3
I_{IX}	1, 2, 3
I_{OZ}	1, 2, 3
I_{CC}	1, 2, 3

Switching Characteristics

Parameter	Subgroups
READ CYCLE	
t_{RC}	7, 8, 9, 10, 11
t_{AA}	7, 8, 9, 10, 11
t_{OHA}	7, 8, 9, 10, 11
t_{ACS}	7, 8, 9, 10, 11
t_{DOE}	7, 8, 9, 10, 11
WRITE CYCLE	
t_{WC}	7, 8, 9, 10, 11
t_{SCS}	7, 8, 9, 10, 11
t_{AW}	7, 8, 9, 10, 11
t_{HA}	7, 8, 9, 10, 11
t_{SA}	7, 8, 9, 10, 11
t_{PWE}	7, 8, 9, 10, 11
t_{SD}	7, 8, 9, 10, 11
t_{HD}	7, 8, 9, 10, 11

Document #: 38–00096–C